FQD1N60C / FQU1N60C

600V N-Channel MOSFET

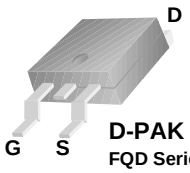
General Description

These N-Channel enhancement mode power field effect transistors are produced using Corise Semiconductorÿs proprietary, planar stripe, DMOS technology.

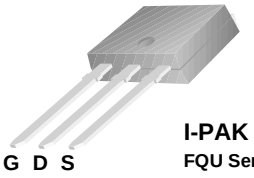
This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency switch mode power supply.

Features

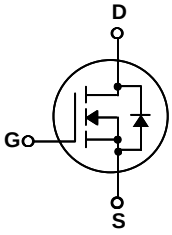
- 1A, 600V, $R_{DS(on)}$ = 11.5Ω @V_{GS} = 10 V
- Low gate charge (typical 4.8nC)
- Low Crss (typical 3.5 pF)
- Fast switching
- 100% avalanche tested
- Improved dv/dt capability



D-PAK
FQD Series



I-PAK
FQU Series



Absolute Maximum Ratings

T_C = 25°C unless otherwise noted

Symbol	Parameter		FQD1N60C / FQU1N60C	Units
V_{DSS}	Drain-Source Voltage		600	V
I_D	Drain Current - Continuous (T_C = 25°C)		1	A
	- Continuous (T_C = 100°C)		0.6	A
I_{DM}	Drain Current - Pulsed	(Note 1)	4	A
V_{GSS}	Gate-Source Voltage		± 30	V
E_{AS}	Single Pulsed Avalanche Energy	(Note 2)	33	mJ
I_{AR}	Avalanche Current	(Note 1)	1	A
E_{AR}	Repetitive Avalanche Energy	(Note 1)	2.8	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	4.5	V/ns
P_D	Power Dissipation (T_A = 25°C)*		2.5	W
	Power Dissipation (T_C = 25°C)		28	W
	- Derate above 25°C		0.22	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range		-55 to +150	°C
T_L	Maximum lead temperature for soldering purposes, 1/8" from case for 5 seconds		300	°C

Thermal Characteristics

Symbol	Parameter	Typ	Max	Units
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case	--	4.53	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient*	--	50	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	--	110	°C/W

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Off Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_D = 250 μA	600	--	--	V
ΔBV_{DSS} / ΔT_J	Breakdown Voltage Temperature Coefficient	I_D = 250 μA, Referenced to 25°C	--	0.6	--	V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 600 V, V_{GS} = 0 V	--	--	1	μA
		V_{DS} = 480 V, T_C = 125°C	--	--	10	μA
I_{GSSF}	Gate-Body Leakage Current, Forward	V_{GS} = 30 V, V_{DS} = 0 V	--	--	100	nA
I_{GSSR}	Gate-Body Leakage Current, Reverse	V_{GS} = -30 V, V_{DS} = 0 V	--	--	-100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250 μA	2.0	--	4.0	V
$R_{DS(on)}$	Static Drain-Source On-Resistance	V_{GS} = 10 V, I_D = 0.5 A	--	9.3	11.5	Ω
g_{FS}	Forward Transconductance	V_{DS} = 40 V, I_D = 0.5 A (Note 4)	--	0.75	--	S
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS} = 25 V, V_{GS} = 0 V, f = 1.0 MHz	--	130	170	pF
C_{oss}	Output Capacitance		--	19	25	pF
C_{rss}	Reverse Transfer Capacitance		--	3.5	4.5	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 300 V, I_D = 1.1 A, R_G = 25 Ω (Note 4, 5)	--	7	24	ns
t_r	Turn-On Rise Time		--	21	52	ns
$t_{d(off)}$	Turn-Off Delay Time		--	13	36	ns
t_f	Turn-Off Fall Time		--	27	64	ns
Q_g	Total Gate Charge	V_{DS} = 480 V, I_D = 1.1 A, V_{GS} = 10 V (Note 4, 5)	--	4.8	6.2	nC
Q_{gs}	Gate-Source Charge		--	0.7	--	nC
Q_{gd}	Gate-Drain Charge		--	2.7	--	nC
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain-Source Diode Forward Current		--	--	1	A
I_{SM}	Maximum Pulsed Drain-Source Diode Forward Current		--	--	4	A
V_{SD}	Drain-Source Diode Forward Voltage	V_{GS} = 0 V, I_S = 0.5 A	--	--	1.4	V
t_{rr}	Reverse Recovery Time	V_{GS} = 0 V, I_S = 1.1 A, dI_F / dt = 100 A/μs (Note 4)	--	190	--	ns
Q_{rr}	Reverse Recovery Charge		--	0.53	--	μC

Notes:
1. Repetitive Rating : Pulse width limited by maximum junction temperature
2. L = 59 mH, I_{AS} = 1.1 A, V_{DD} = 50V, R_G = 25 Ω, Starting T_J = 25°C
3. I_{SD} ≤ 1.1 A, di/dt ≤ 200A/μs, V_{DD} ≤ BV_{DSS}, Starting T_J = 25°C
4. Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2%
5. Essentially independent of operating temperature

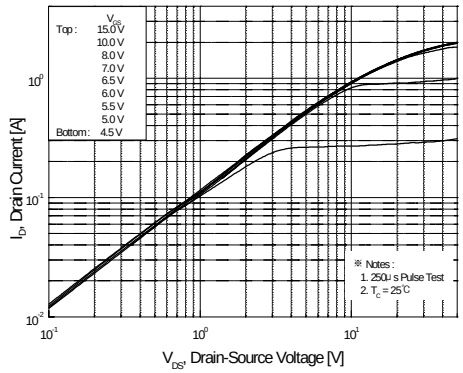


Figure 1. On-Region Characteristics

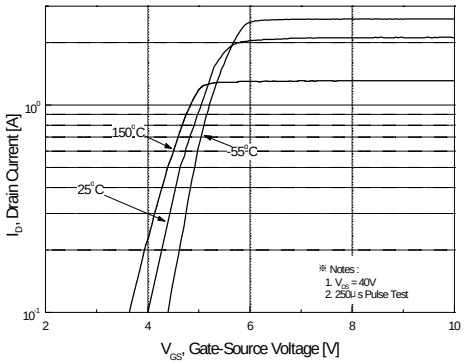


Figure 2. Transfer Characteristics

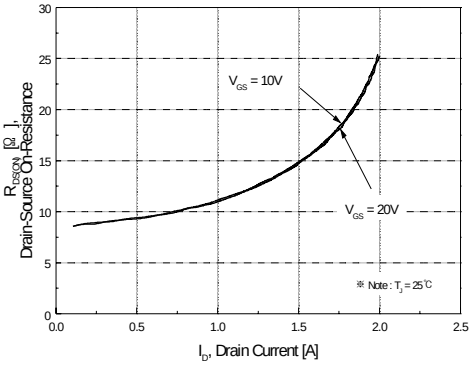


Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage

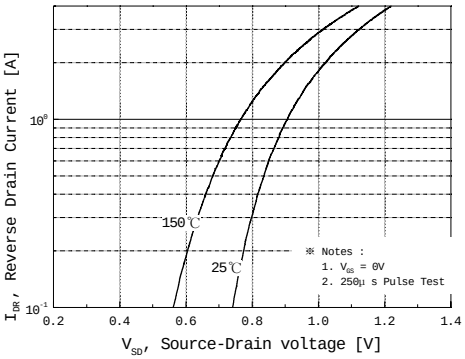


Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature

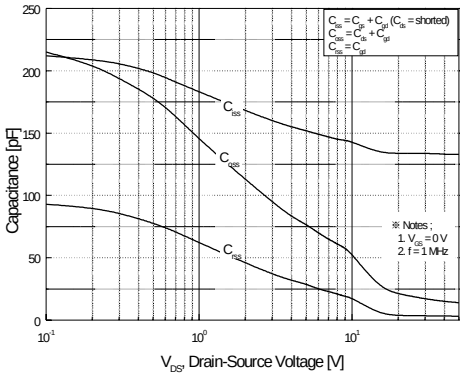


Figure 5. Capacitance Characteristics

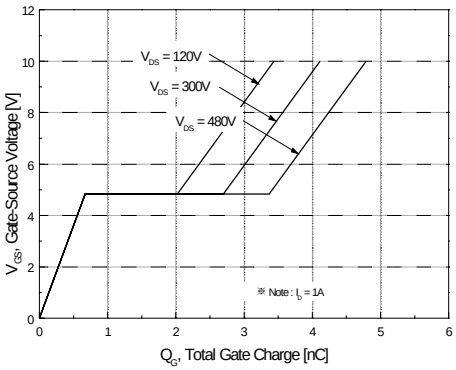


Figure 6. Gate Charge Characteristics

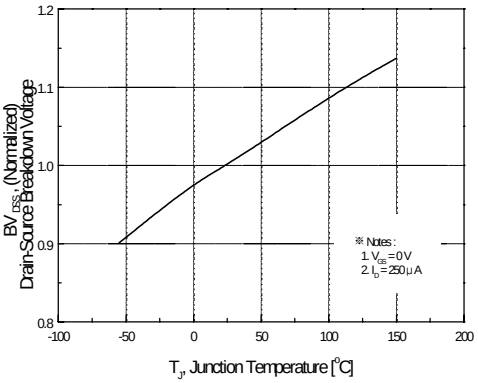


Figure 7. Breakdown Voltage Variation vs Temperature

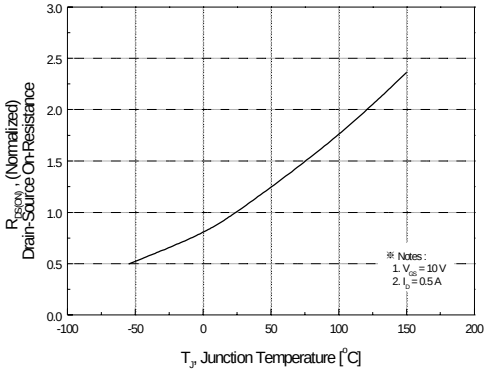


Figure 8. On-Resistance Variation vs Temperature

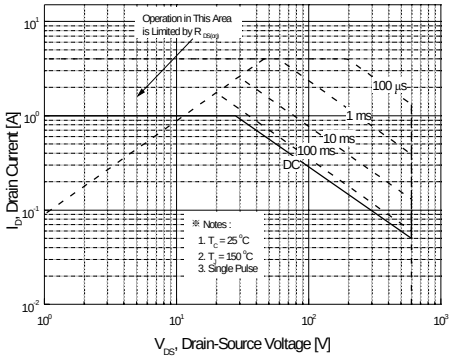


Figure 9. Maximum Safe Operating Area

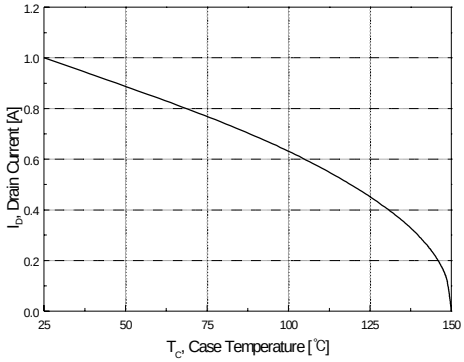


Figure 10. Maximum Drain Current vs Case Temperature

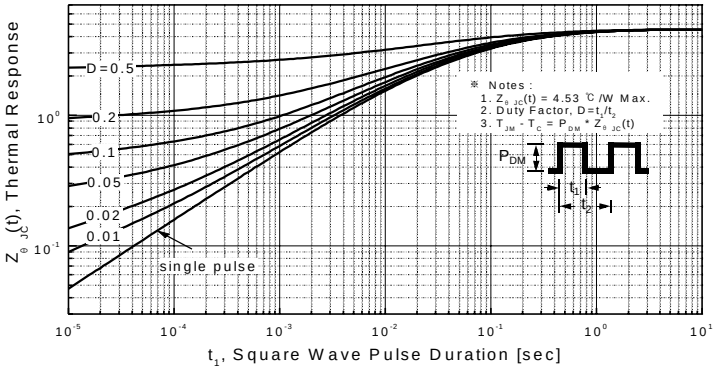
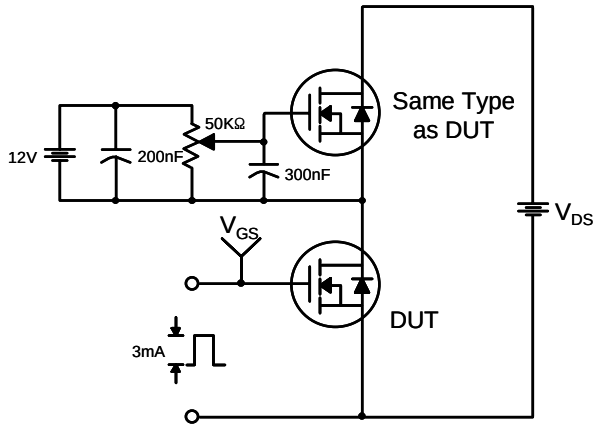
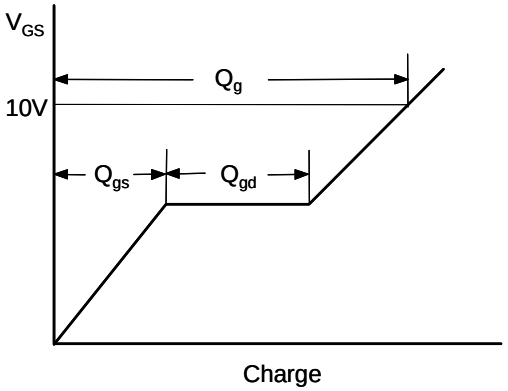
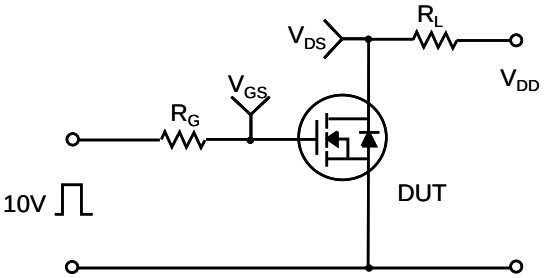


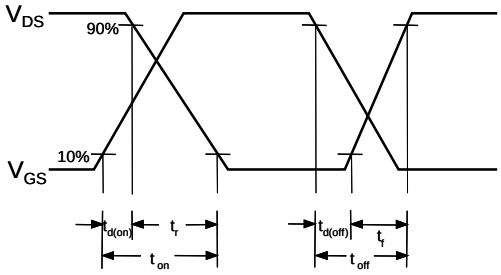
Figure 11. Transient Thermal Response Curve



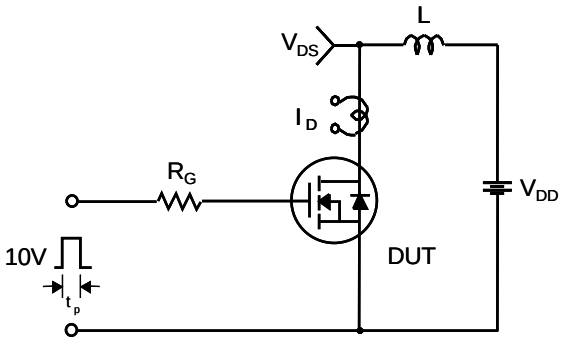


Resistive Switching Test Circuit & Waveforms

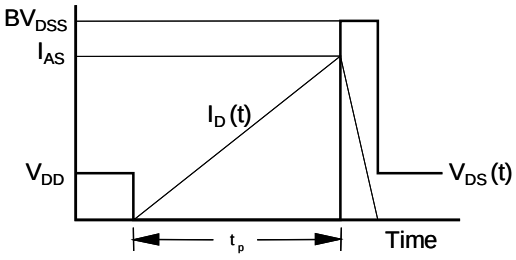


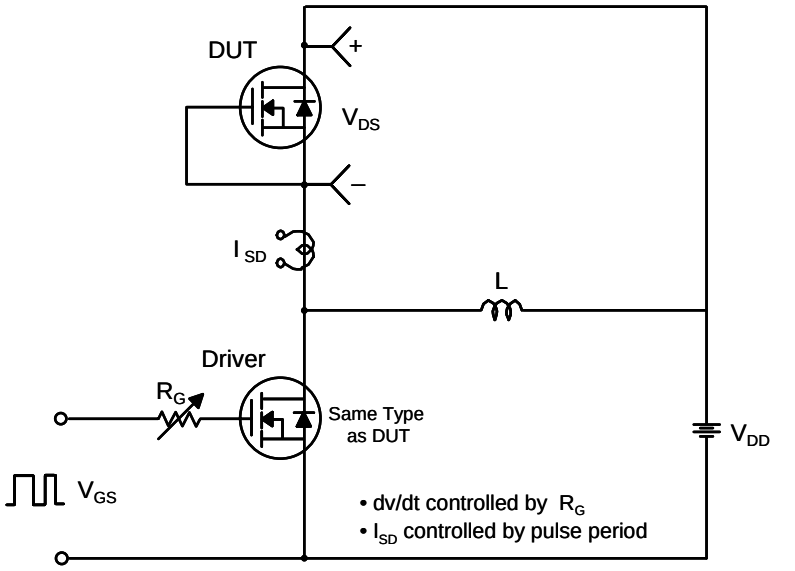


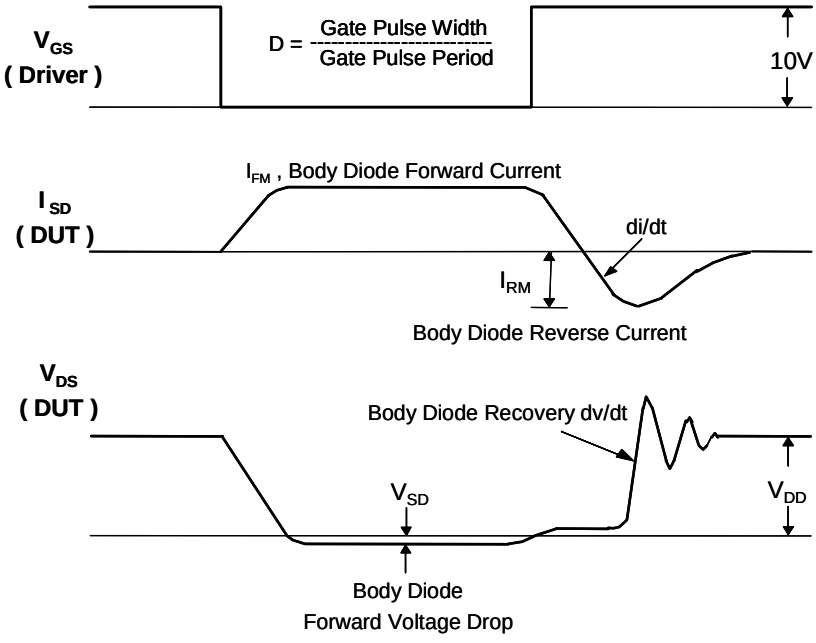
Unclamped Inductive Switching Test Circuit & Waveforms



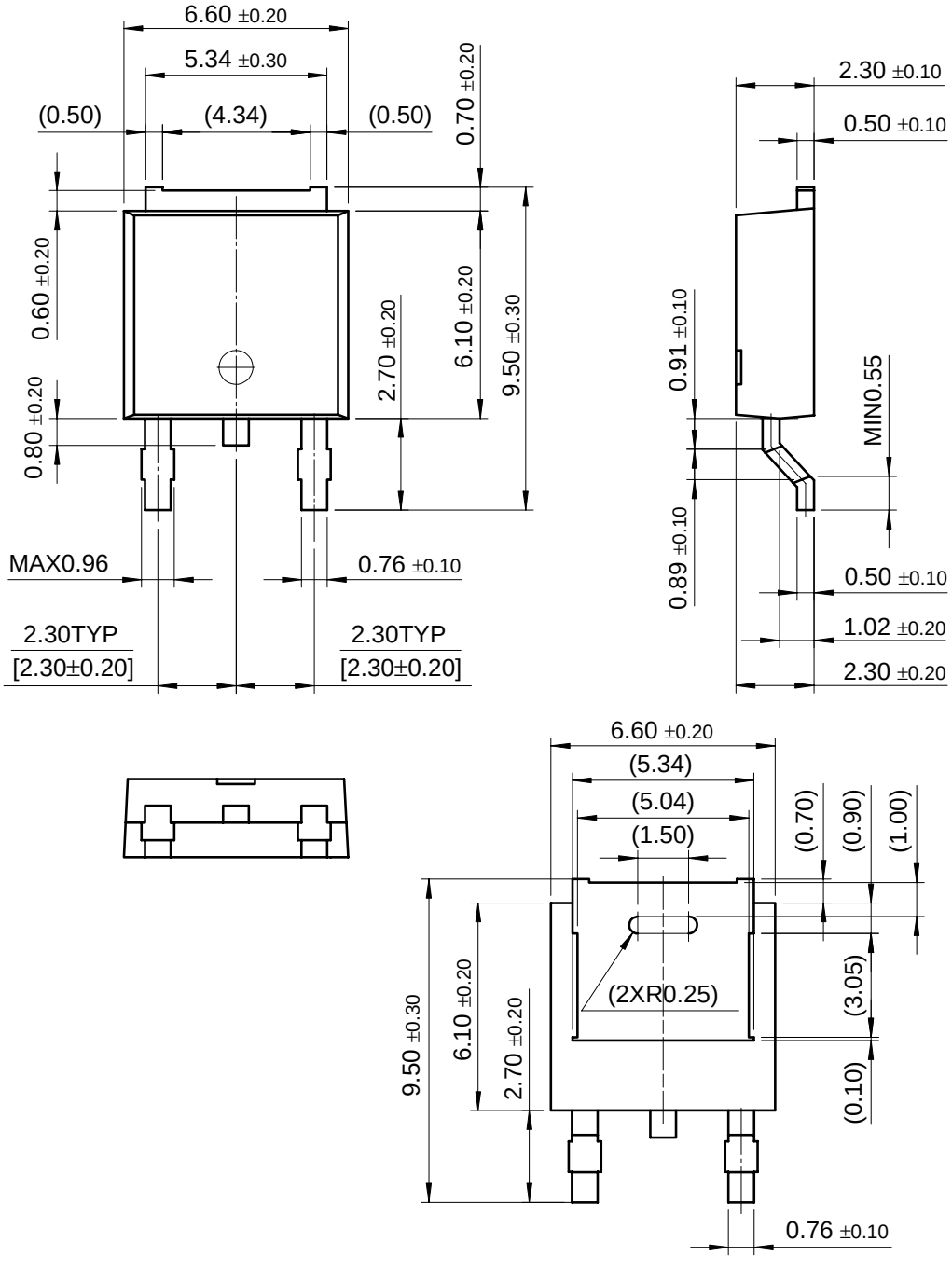
$$E_{AS} = \frac{1}{2} L I_{AS}^2 \frac{BV_{DSS}}{BV_{DSS} - V_{DD}}$$



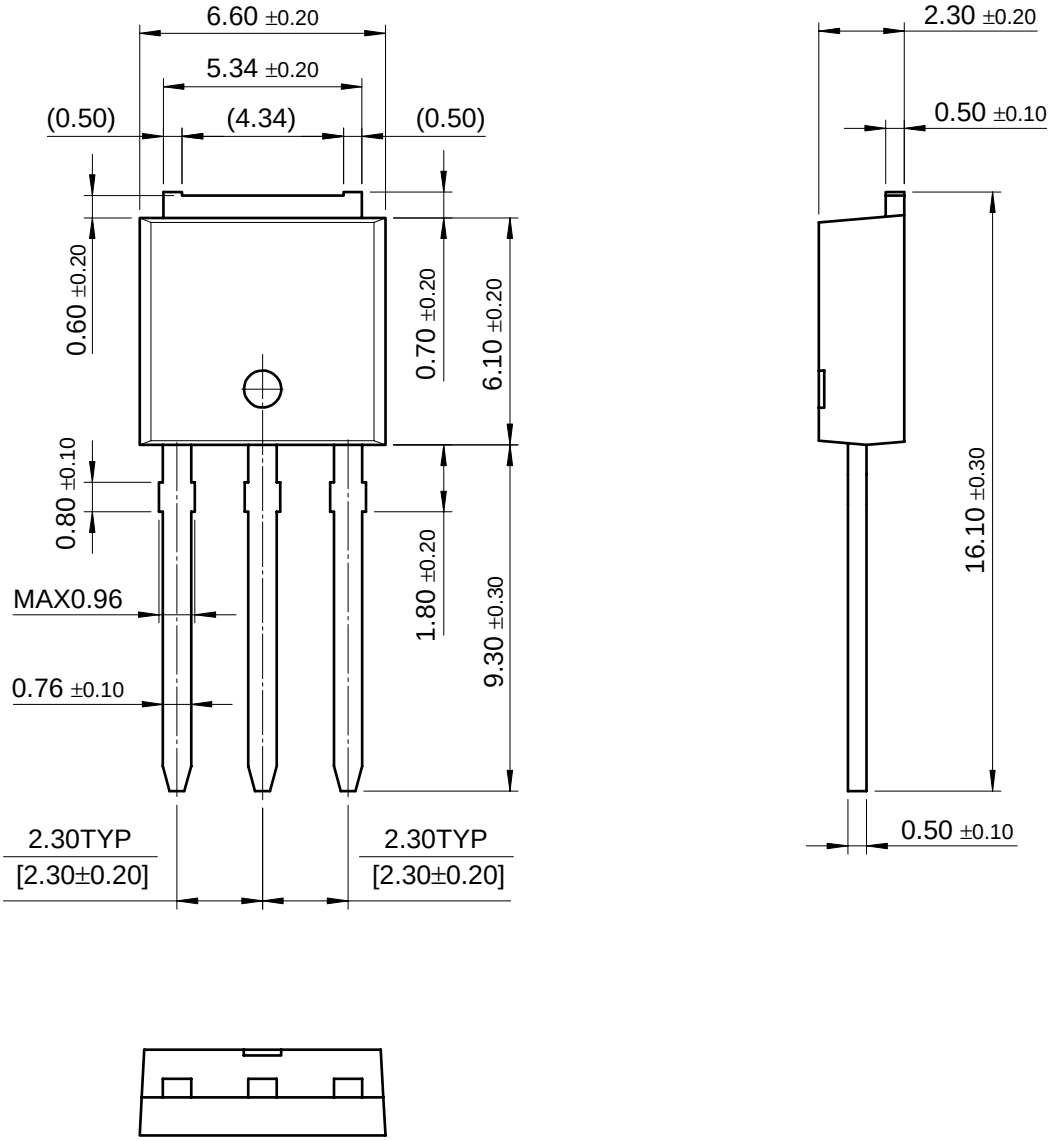

DUT
+
V_{DS}
–
I_{SD}
L
Driver
R_G
Same Type
as DUT
V_{DD}
V_{GS}
• dv/dt controlled by R_G
• I_{SD} controlled by pulse period


V_{GS}
(Driver)
D = Gate Pulse Width / Gate Pulse Period
10V
I_{FM} , Body Diode Forward Current
I_{SD}
(DUT)
di/dt
I_{RM}
Body Diode Reverse Current
V_{DS}
(DUT)
Body Diode Recovery dv/dt
V_{SD}
V_{DD}
Body Diode
Forward Voltage Drop

D-PAK


6.60 ±0.20
5.34 ±0.30
(0.50)
(4.34)
(0.50)
0.70 ±0.20
0.60 ±0.20
0.80 ±0.20
2.70 ±0.20
6.10 ±0.20
9.50 ±0.30
MAX0.96
0.76 ±0.10
2.30TYP
[2.30±0.20]
2.30TYP
[2.30±0.20]
2.30 ±0.10
0.50 ±0.10
0.91 ±0.10
MIN0.55
0.89 ±0.10
0.50 ±0.10
1.02 ±0.20
2.30 ±0.20
6.60 ±0.20
(5.34)
(5.04)
(1.50)
(0.70)
(0.90)
(1.00)
(2XR0.25)
(3.05)
(0.10)
9.50 ±0.30
6.10 ±0.20
2.70 ±0.20
0.76 ±0.10

I-PAK


6.60 ±0.20
5.34 ±0.20
(0.50)
(4.34)
(0.50)
0.60 ±0.20
0.70 ±0.20
6.10 ±0.20
0.80 ±0.10
1.80 ±0.20
9.30 ±0.30
MAX0.96
0.76 ±0.10
2.30TYP
[2.30±0.20]
2.30TYP
[2.30±0.20]
2.30 ±0.20
0.50 ±0.10
16.10 ±0.30
0.50 ±0.10

Общество с ограниченной ответственностью «МосЧип» ИНН 7719860671 / КПП 771901001
Адрес: 105318, г.Москва, ул.Щербаковская д.3, офис 1107

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

http://moschip.ru/get-element

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:
moschip.ru
moschip.ru_4
moschip.ru_6
moschip.ru_9